Listing of the Claims:

Claims 1-5 (Canceled).

Claim 6 (Currently amended): A method for forming a trench isolation comprising the steps of:

forming a planarization stop layer on a semiconductor substrate on which a pad oxide layer is formed;

forming a trench in the semiconductor substrate by etching sequentially a part of the planarization stop layer, a part of the pad oxide film, and a part of the semiconductor substrate;

performing a thermal oxidation process ~~for the semiconductor substrate in which the trench is formed~~ to form a thermal oxide film on bottom and sidewall surfaces of the trench and on a sidewall and a top surface of the planarization stop film;

filling the trench with a trench fill insulating material in which the thermal oxidation process is performed;

planarizing the trench fill insulating material such that the planarization stop layer is exposed;

recessing the trench fill insulating material to under the planarization stop film; and

forming a trench oxidation-preventive film on the recessed trench fill insulating material.

Claim 7 (Currently amended): The method of claim 6, ~~wherein~~ further comprising planarizing the oxidation-preventive to a ~~the~~ level ~~of the trench oxidation-preventive film~~ that is substantially even with an upper surface of the planarization stop film ~~after planarizing~~.

Claim 8 (Original): The method of claim 6, wherein the planarization stop film is made of a silicon layer, and the trench oxidation-preventive film is made of a silicon nitride film.

Claim 9 (Original): A method for forming a trench isolation comprising the steps of:

forming a planarization stop film on a semiconductor substrate on which a pad oxide film is formed;

forming a trench by etching sequentially a part of the planarization stop film, a part of the pad oxidation film, and a part of the semiconductor substrate;

forming a thermal oxide film on a bottom and a sidewall of the trench, and on a sidewall and a top surface of the planarization stop film;

filling the trench with a trench fill insulating material on the thermal oxide film to completely fill the trench;

planarization the trench fill insulating material such that the planarization stop film is exposed;

recessing the planarized trench fill insulating material under the planarization stop film;

forming a trench oxidation-preventive film on the recessed trench fill insulating material; and

removing the planarization stop film and the pad oxide film.

Claim 10 (Original): The method of claim 9, wherein the planarization stop film is made of a silicon film.

Claim 11 (Original): The method of claim 9, wherein the trench oxidation-preventive film is made of a silicon nitride film.

Claim 12 (Original): The method of claim 9, wherein the step of filling the trench is performed in a same facility for the step of the forming the thermal oxide film.

Claim 13 (Original): The method of claim 9, wherein the step of recessing the planarized trench fill insulating material exposes a sidewall of the planarization stop film, and recesses substantially to an interface between the planarization stop film and the pad oxidation film.

Claim 14 (Original): The method of claim 9, wherein the step of forming the oxidation-preventive film comprises the steps of:

forming an oxidation-preventive material film on the planarization stop film and the recessed trench fill insulating material; and

planarizing the oxidation-preventive material film such that the planarization stop film is exposed.

Claim 15 (Original): The method of claim 14, the method further comprising a step of forming a buffer oxidation film on the oxidation-preventive material film.

Claim 16 (Original): The method of claim 9, the method further comprising the steps of:

forming a gate oxidation film on the semiconductor substrate on which the planarization stop film and the pad oxide film are removed;

forming a gate electrode material on the gate oxidation film and the trench oxidation-preventive film;

forming a gate line extending to one direction by patterning the gate electrode material;

forming a sidewall spacer insulating film over an entire surface of the consequence where the gate line is formed; and

forming an insulating spacer on a sidewall of the gate line by etching the sidewall spacer insulating film,

wherein the trench oxidation-preventive film on both sides of the gate line is etched concurrently with the sidewall spacer insulating film, leaving the oxidation-preventive film only on the trench under the gate line and the sidewall spacer insulating film.

Claim 17 (Original): The method of claim 9, wherein the thermal oxidation film is formed on the sidewall and the top surface of the planarization stop film thicker than that on the bottom and the sidewall of the trench.

Claim 18 (New): A method for forming a trench isolation comprising the steps of:

forming a planarization stop layer on a semiconductor substrate on which a pad oxide layer is formed;

forming a trench in the semiconductor substrate by etching sequentially a part of the planarization stop layer, a part of the pad oxide film, and a part of the semiconductor substrate;

performing a thermal oxidation process for the semiconductor substrate in which the trench is formed;

filling the trench with a trench fill insulating material in which the thermal oxidation process is performed;

planarizing the trench fill insulating material such that the planarization stop layer is exposed;

recessing the trench fill insulating material to a level substantially even with an upper surface of the pad oxide layer; and

forming a trench oxidation-preventive film on the recessed trench fill insulating material.

Claim 19 (New): The method of claim 18, further comprising planarizing the trench oxidation-preventive film to a level that is substantially even with an upper surface of the planarization stop film.

Claim 20 (New): The method of claim 18, wherein the planarization stop film is made of a silicon layer, and the trench oxidation-preventive film is made of a silicon nitride film.